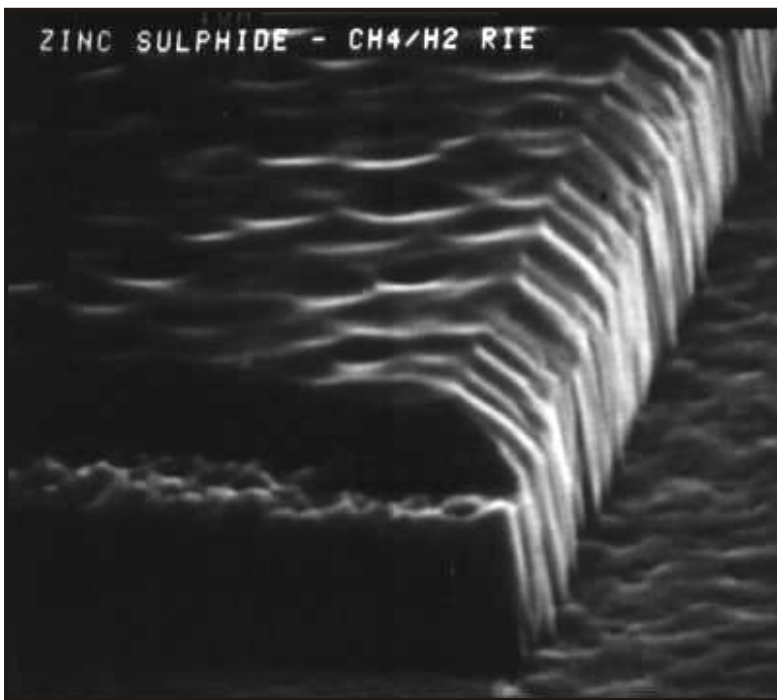
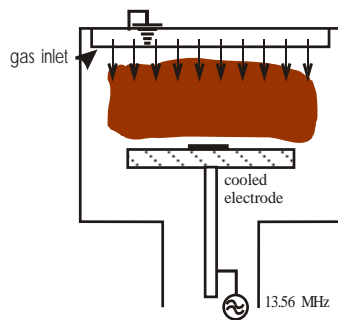


Plasmalab Data

ZnS - (MO) RIE



0.85 µm deep, anisotropic Etch in ZnS (Photoresist mask intact)



- Plasmalab 80 Plus*
- Plasmalab 800 Plus*
- Plasmalab System 100*
- Plasmalab System 133*

Technology:

- Reactive Ion Etching
- 13 MHz Plasma Excitation
- Parallel Plate Reactor

Results:

- Rate : ca. 20 nm / min
- Profil: anisotropic
- Surface: low roughness
- Uniformity: +/- 5 % (75 mm)
- Mask: Photoresist

